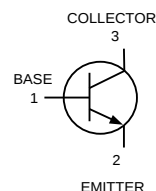
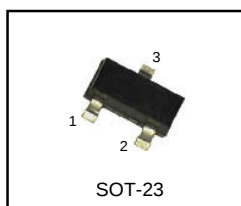


**General Purpose Transistor**  
**NPN Silicon**  
**Halogen-free type**  
**Lead free product**

**MMBT2222AGH**



**MAXIMUM RATINGS**

| Rating                       | Symbol           | Value | Unit             |
|------------------------------|------------------|-------|------------------|
| Collector-Emitter Voltage    | V <sub>CEO</sub> | 40    | V <sub>dc</sub>  |
| Collector-Base Voltage       | V <sub>CBO</sub> | 75    | V <sub>dc</sub>  |
| Emitter-Base Voltage         | V <sub>EBO</sub> | 6.0   | V <sub>dc</sub>  |
| Collector Current-Continuous | I <sub>C</sub>   | 600   | mA <sub>dc</sub> |

**THERMAL CHARACTERISTICS**

| Characteristic                                                                          | Symbol                            | Max.        | Unit          |
|-----------------------------------------------------------------------------------------|-----------------------------------|-------------|---------------|
| Total Device Dissipation FR-5 Board <sup>(1)</sup> TA=25°C<br>Derate above 25°C         | P <sub>D</sub>                    | 225<br>1.8  | mW<br>mW / °C |
| Thermal Resistance Junction to Ambient                                                  | R <sub>θJA</sub>                  | 556         | °C / W        |
| Total Device Dissipation Alumina Substrate, <sup>(2)</sup> TA=25°C<br>Derate above 25°C | P <sub>D</sub>                    | 300<br>2.4  | mW<br>mW / °C |
| Thermal Resistance Junction to Ambient                                                  | R <sub>θJA</sub>                  | 417         | °C / W        |
| Junction and Storage Temperature                                                        | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C            |

**ELECTRICAL CHARACTERISTICS** (TA=25°C unless otherwise noted)

| Characteristic | Symbol | Min. | Max. | Unit |
|----------------|--------|------|------|------|
|----------------|--------|------|------|------|

**OFF CHARACTERISTICS**

|                                                                                                                                                                               |                      |        |            |                  |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------|--------|------------|------------------|
| Collector-Emitter Breakdown Voltage<br>( I <sub>C</sub> =10mA <sub>dc</sub> , I <sub>B</sub> =0 )                                                                             | V <sub>(BR)CEO</sub> | 40     | -          | V <sub>dc</sub>  |
| Collector-Emitter Breakdown Voltage<br>( I <sub>C</sub> =10mA <sub>dc</sub> , I <sub>E</sub> =0 )                                                                             | V <sub>(BR)CBO</sub> | 75     | -          | V <sub>dc</sub>  |
| Emitter - Base Breakdown Voltage<br>( I <sub>E</sub> =10 mA <sub>dc</sub> , I <sub>C</sub> =0 )                                                                               | V <sub>(BR)EBO</sub> | 6.0    | -          | V <sub>dc</sub>  |
| Collector Cutoff Current<br>( V <sub>CE</sub> =60 V <sub>dc</sub> , V <sub>EB</sub> (off)=3.0 V <sub>dc</sub> )                                                               | I <sub>CEX</sub>     | -      | 10         | nA <sub>dc</sub> |
| Collector Cutoff Current<br>( V <sub>CB</sub> =60 V <sub>dc</sub> , I <sub>E</sub> =0 )<br>( V <sub>CB</sub> =60 V <sub>dc</sub> , I <sub>E</sub> =0, T <sub>A</sub> =125°C ) | I <sub>CBO</sub>     | -<br>- | 0.01<br>10 | uA <sub>dc</sub> |
| Emitter Cutoff Current ( V <sub>EB</sub> =3.0 V <sub>dc</sub> , I <sub>C</sub> =0 )                                                                                           | I <sub>EBO</sub>     | -      | 100        | nA <sub>dc</sub> |
| Base Cutoff Current ( V <sub>CE</sub> =60 V, V <sub>EB</sub> (off)=3.0 V <sub>dc</sub> )                                                                                      | I <sub>BL</sub>      | -      | 20         | nA <sub>dc</sub> |

(1) FR-5=1.0 × 0.75 × 0.062in.

(2) Alumina=0.4 × 0.3 × 0.024in. 99.5% alumina.

**ELECTRICAL CHARACTERISTICS** (TA=25°C unless otherwise noted) (Continued)

| Characteristic | Symbol | Min. | Max. | Unit |
|----------------|--------|------|------|------|
|----------------|--------|------|------|------|

**ON CHARACTERISTICS<sup>(3)</sup>**

|                                                                                                                                                                                                                                                                                                |          |                                         |                                   |     |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------|-----------------------------------------|-----------------------------------|-----|
| DC Current Gain<br>( IC=0.1 mAdc, VCE=10 Vdc )<br>( IC=1.0 mAdc, VCE=10 Vdc )<br>( IC=10 mAdc, VCE=10 Vdc )<br>( IC=10 mAdc, VCE=10 Vdc, TA=-55°C )<br>( IC=150 mAdc, VCE=10 Vdc ) <sup>(3)</sup><br>( IC=150 mAdc, VCE=1.0 Vdc ) <sup>(3)</sup><br>( IC=500 mAdc, VCE=10 Vdc ) <sup>(3)</sup> | HFE      | 35<br>50<br>75<br>35<br>100<br>50<br>40 | -<br>-<br>-<br>-<br>300<br>-<br>- | -   |
| Collector-Emitter Saturation Voltage <sup>(3)</sup><br>( IC=150 mAdc, IB=15 mAdc )<br>( IC=500 mAdc, IB=50 mAdc )                                                                                                                                                                              | VCE(sat) | -<br>-                                  | 0.3<br>1.0                        | Vdc |
| Base-Emitter Saturation Voltage <sup>(3)</sup><br>( IC=150 mAdc, IB=15 mAdc )<br>( IC=500 mAdc, IB=50 mAdc )                                                                                                                                                                                   | VBE(sat) | 0.6<br>-                                | 1.2<br>2.0                        | Vdc |

**SMALL-SIGNAL CHARACTERISTIC**

|                                                                                                              |        |             |             |                    |
|--------------------------------------------------------------------------------------------------------------|--------|-------------|-------------|--------------------|
| Current-Gain-Bandwidth Product <sup>(4)</sup><br>( IC=20 mAdc, VCE=20 Vdc, f=100 MHz )                       | fT     | 300         | -           | MHz                |
| Output Capacitance<br>( VCB=10 Vdc, IE=0, f=1.0 MHz )                                                        | Cobo   | -           | 8.0         | pF                 |
| Input Capacitance<br>( VEB=0.5 Vdc, IC=0, f=1.0 MHz )                                                        | Cibo   | -           | 25          | pF                 |
| Input Impedance<br>( VCE=10 Vdc, IC=1.0 mAdc, f=1.0 kHz )<br>( VCE=10 Vdc, IC=10 mAdc, f=1.0 kHz )           | hie    | 2.0<br>0.25 | 8.0<br>1.25 | k ohms             |
| Voltage Feedback Ratio<br>( VCE=10 Vdc, IC=1.0 mAdc, f=1.0 kHz )<br>( VCE=10 Vdc, IC=10 mAdc, f=1.0 kHz )    | hre    | -<br>-      | 8.0<br>4.0  | X 10 <sup>-4</sup> |
| Small-Signal Current Gain<br>( VCE=10 Vdc, IC=1.0 mAdc, f=1.0 kHz )<br>( VCE=10 Vdc, IC=10 mAdc, f=1.0 kHz ) | hfe    | 50<br>75    | 300<br>375  | -                  |
| Output Admittance<br>( VCE=10 Vdc, IC=1.0 mAdc, f=1.0 kHz )<br>( VCE=10 Vdc, IC=10 mAdc, f=1.0 kHz )         | hoe    | 5.0<br>25   | 35<br>200   | u mhos             |
| Collector Base Time Constant<br>( VCB=10 Vdc, IC=100 uAdc, RS = 1.0 k ohms, f=1.0 kHz )                      | rb, Cc | -           | 150         | ps                 |
| Noise Figure<br>( VCE=10 Vdc, IC=100 uAdc, RS=1.0 k ohm, f=1.0 kHz )                                         | NF     | -           | 4.0         | dB                 |

**SWITCHING CHARACTERISTICS**

|              |                                                                      |    |   |     |    |
|--------------|----------------------------------------------------------------------|----|---|-----|----|
| Delay Time   | ( VCC=30 Vdc, VBE (off) = -0.5 Vdc,<br>IC =150 mAdc, IB1 = 15 mAdc ) | td | - | 10  | nS |
| Rise Time    |                                                                      | tr | - | 25  |    |
| Storage Time | ( VCC=30 Vdc, IC = 150 mAdc,<br>IB1 =IB2 = 15 mAdc )                 | ts | - | 225 | nS |
| Fall Time    |                                                                      | tf | - | 60  |    |

(3) Pulse Test : Pulse Width ≤ 300 uS, Duty Cycle ≤ 2.0%.

(2) fT is defined as the frequency at which hfe extrapolates to unity.

# SWITCHING TIME EQUIVALENT TEST CIRCUITS

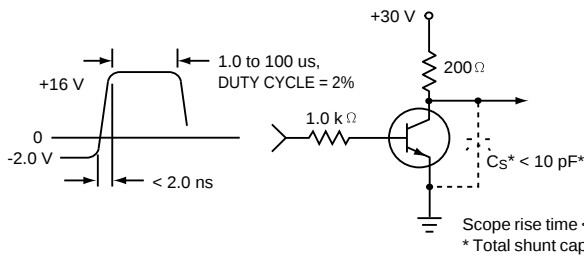


Figure 1. Turn-On Time

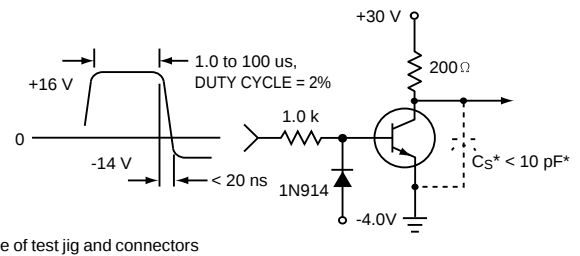


Figure 2. Turn-Off Time

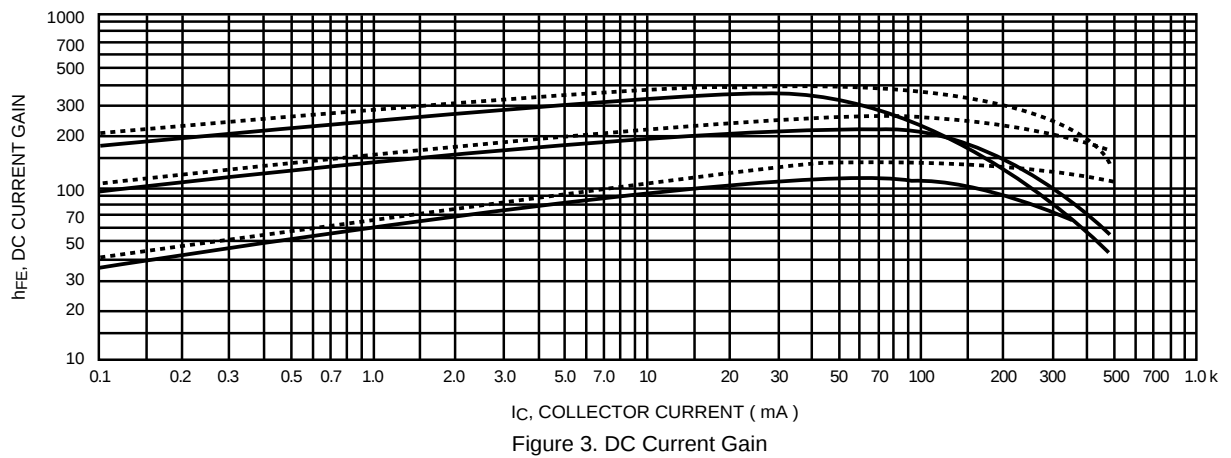


Figure 3. DC Current Gain

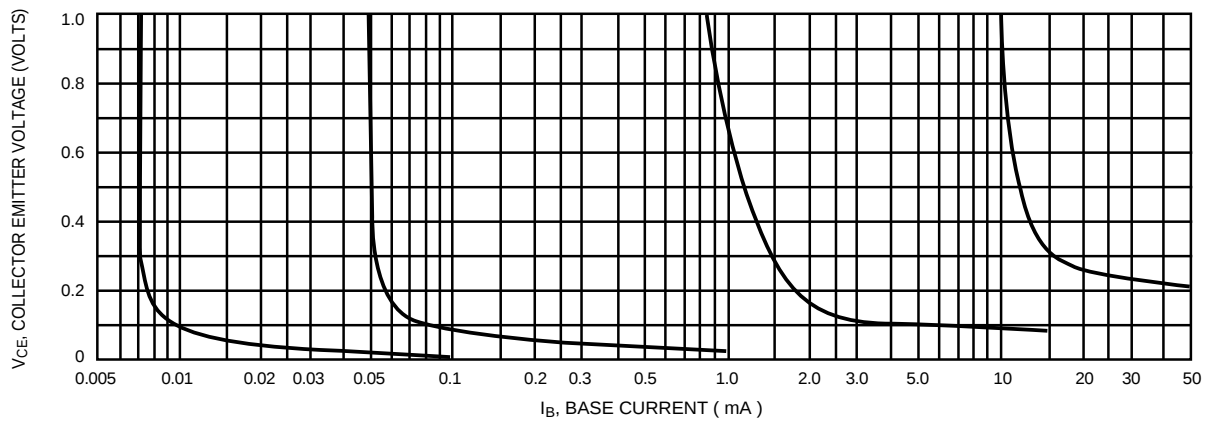
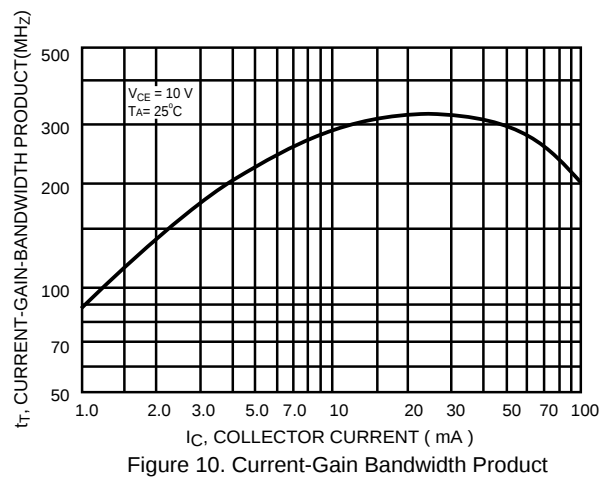
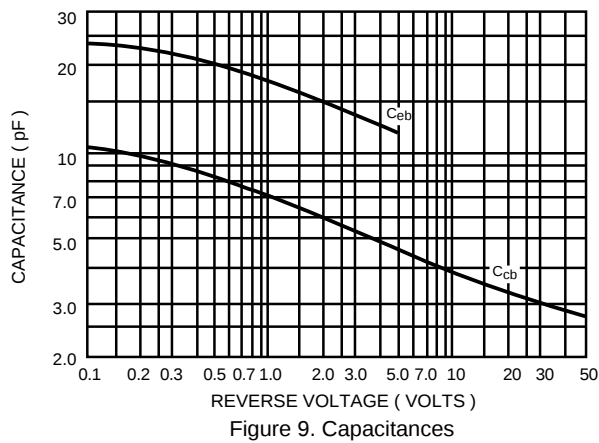
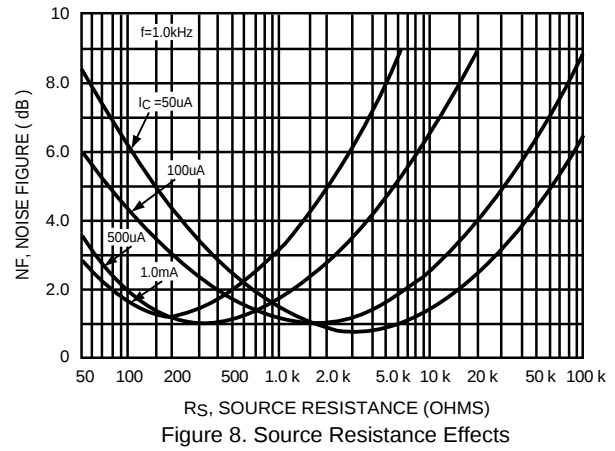
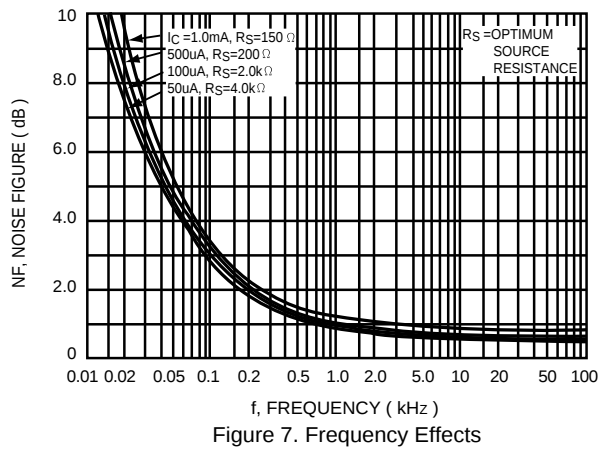
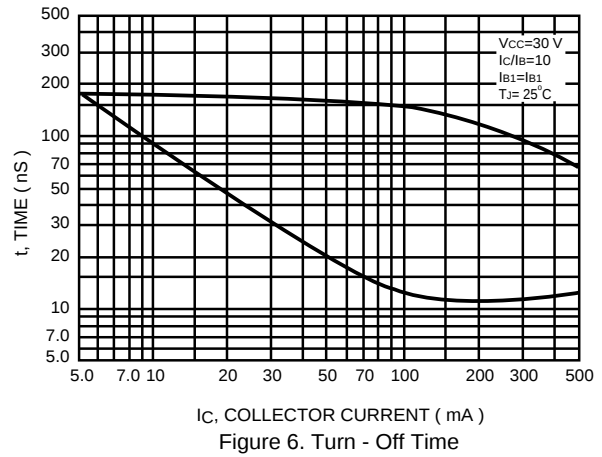
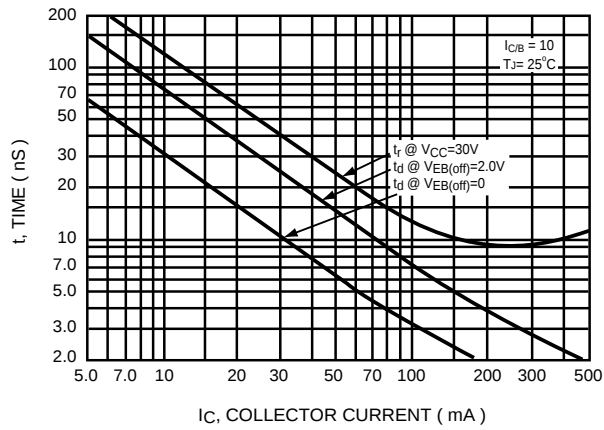


Figure 4. Collector Saturation Region



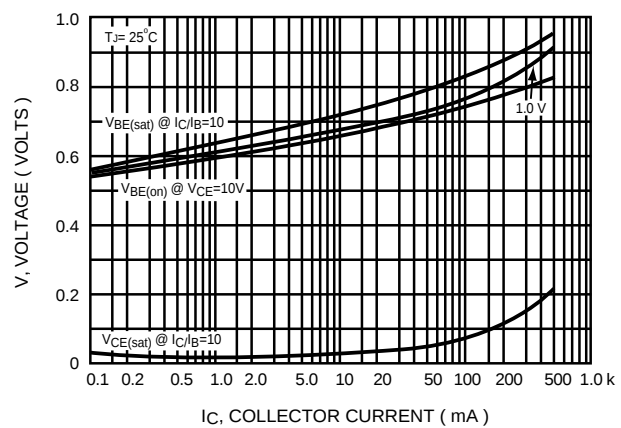


Figure 11. "On" Voltage

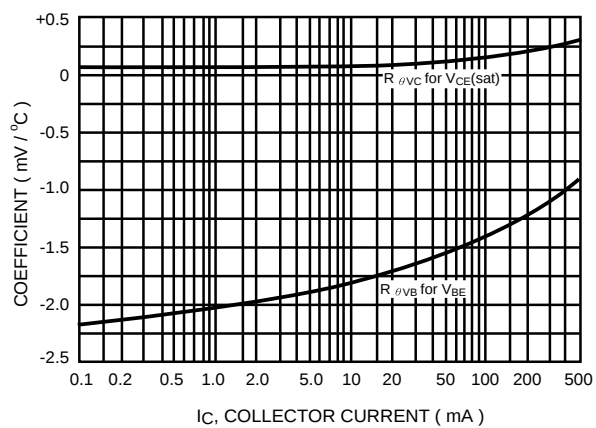


Figure 12. Temperature Coefficients